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# N-Channel 100 V (D-S) MOSFET

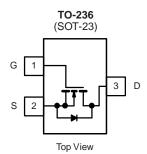
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)		
100	0.275 at V <sub>GS</sub> = 10 V	0.9		

#### **FEATURES**

- Halogen-free According to IEC 61249-2-21
- 100 % R<sub>g</sub> and UIS Tested
  TrenchFET<sup>®</sup> Power MOSFET
- Compliant to RoHS Directive 2002/95/EC







<b>ABSOLUTE MAXIMUM RATINGS</b>	(T <sub>A</sub> = 25 °C, unle	ess otherwise	noted)		_
Parameter		Symbol		Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	100		V
Gate-Source Voltage		$V_{GS}$	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	- I <sub>D</sub>		0.9	۸
	T <sub>A</sub> = 70 °C			0.8	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	6		Α
Avalanche Current <sup>b</sup>	L = 0.1 mH	I <sub>AS</sub>	6		İ
Single Avalanche Energy	L = 0.1 IIII	E <sub>AS</sub>	1.	.8	mJ
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	0.6		Α
Dower Dissipation <sup>8</sup>	T <sub>A</sub> = 25 °C	В	1.25	0.73	W
Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	P <sub>D</sub>	0.80	0.47	VV
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stq</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 5 s	- R <sub>thJA</sub>	80	100	°C/W	
	Steady State		130	170		
Maximum Junction-to-Foot	Steady State		45	55		

## Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. Pulse width limited by maximum junction temperature.

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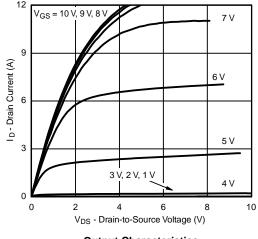
			Limits				
Parameter	Symbol	Test Conditions	Min. Typ. Max.			Unit	
Static	Syllibol	rest conditions	I WIIII.	тур.	IVIAA.	Oilit	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1 mA	100	1			
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	2		4	V	
Gate-Body Leakage		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	_		± 100	nA	
Gale-Body Leakage	I <sub>GSS</sub>				1	ПА	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V				μΑ	
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C			75		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 15 \text{ V}, V_{GS} = 10 \text{ V}$	6			Α	
Drain-Source On-Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_D = 0.5 \text{ A}$		0.275		Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_D = 0.5 \text{ A}$		4		S	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> = 0.5 A, V <sub>GS</sub> = 0 V		0.8	1.2	V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg			3.3		nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 0.5 \text{ A}$		0.47			
Gate-Drain Charge	Q <sub>gd</sub>			1.45		1	
Gate Resistance	$R_g$			1.3		Ω	
Switching							
Turn-On Delay Time	t <sub>d(on)</sub>			7			
Rise Time	t <sub>r</sub>	$V_{DD}$ = 50 V, $R_L$ = 33 $\Omega$		11		ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 0.2 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 6 \Omega$		9			
Fall Time	t <sub>f</sub>			10			
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	$I_F = 0.5 \text{ A}, dI/dt = 100 \text{ A/}\mu\text{s}$		50			

#### Notes:

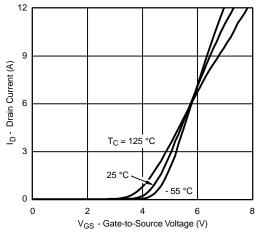
- a. Pulse test: PW  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



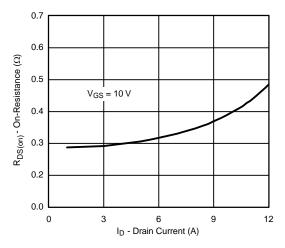




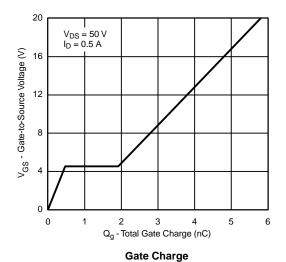
**Transfer Characteristics** 



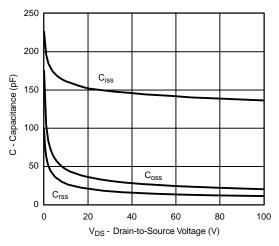
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



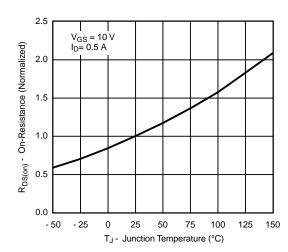
#### On-Resistance vs. Drain Current



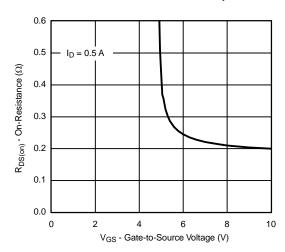
Source-Drain Diode Forward Voltage



Capacitance



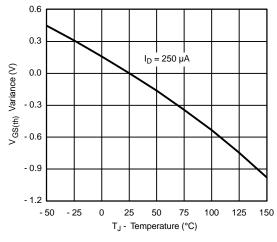
On-Resistance vs. Junction Temperature

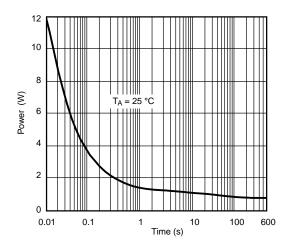


On-Resistance vs. Gate-to-Source Voltage



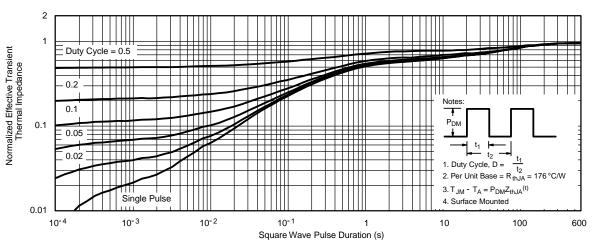
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





**Threshold Voltage** 





Normalized Thermal Transient Impedance, Junction-to-Ambient





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